DSA30C200IB

Schottky Diode Gen²

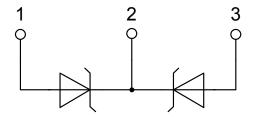
		preliminary
V_{RRM}	=	200 V
l _{fav}	= 2x	15A
V _F	=	0.78V

High Performance Schottky Diode Low Loss and Soft Recovery **Common Cathode**

Part number **DSA30C200IB**



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation Low voltage peaks for reduced
- protection circuits
- · Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-262 (I2Pak)

- · Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IXYS reserves the right to change limits, conditions and dimensions.

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Schottk	у				Ratings	6	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	$V_{R} = 200 V$	$T_{VJ} = 25^{\circ}C$			250	μA
		$V_{R} = 200 V$	$T_{v_{J}} = 125^{\circ}C$			2.5	mA
V _F	forward voltage drop	I _F = 15 A	$T_{VJ} = 25^{\circ}C$			0.94	V
		I _F = 30 A				1.10	V
		I _F = 15 A	T _{vJ} = 125°C			0.78	V
		I _F = 30 A				0.95	V
I FAV	average forward current	T _c = 155°C	T _{vJ} = 175°C			15	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.53	V
r _F	slope resistance } for power lo	oss calculation only				10.8	mΩ
R _{thJC}	thermal resistance junction to case	9				1.75	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.50		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			85	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0 V$	$T_{vJ} = 45^{\circ}C$			320	Α
C	junction capacitance	V_{R} = 48 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		47		pF

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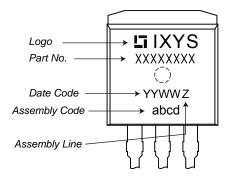


DSA30C200IB

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Package TO-262 (I2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)			35	Α
T _{vj}	virtual junction temperature		-55		175	°C
T _{op}	operation temperature		-55		150	°C
T _{stg}	storage temperature		-55		150	°C
Weight				1.5		g
Fc	mounting force with clip		20		60	Ν





Part number

- D = Diode S = Schottky Diode
- A = low VF
- 30 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V] IB = TO-262 (I2Pak) (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA30C200IB	DSA30C200IB	Tube	50	512200

Similar Part	Package	Voltage class
DSA30C200PB	TO-220AB (3)	200

Equiva	lent Circuits for	Simulation	* on die level	T _{vJ} = 175 °C
	$-R_0$	Schottky		
V _{0 max}	threshold voltage	0.53		V
$R_{0 max}$	slope resistance *	7.6		mΩ

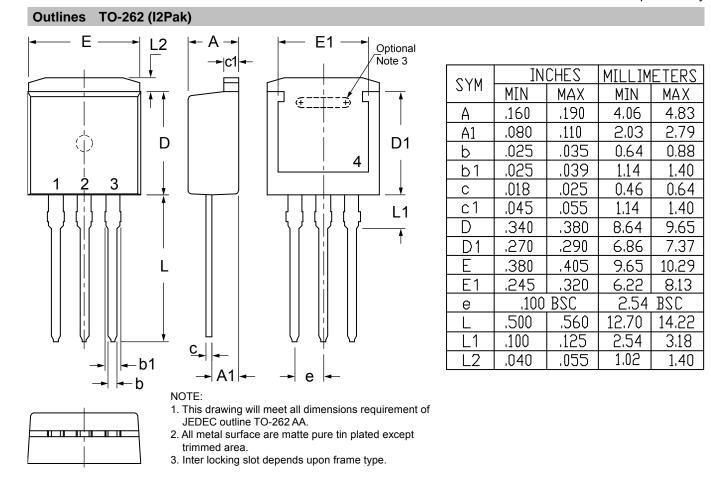
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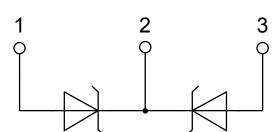
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